

# Solution sheet - Tute-9, Laser Technology.

Q1)  $\lambda = 10.6 \mu\text{m} = \frac{hc}{E} \Rightarrow E = 1.875 \times 10^{-20} \text{ J} \Rightarrow t = \frac{E}{P} = 1.875 \times 10^{-23} \text{ s}$

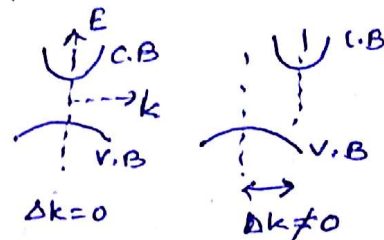
So number of Photons emitted in 1 minute =  $\frac{60}{1.875 \times 10^{-23}} = 3.2 \times 10^{23}$

Q2) Input power =  $2 \times 230 \text{ W} = 460 \text{ W}$ , } Efficiency =  $\frac{\text{Output}}{\text{Input}} \times 100 = \frac{10 \times 10^{-3} \text{ W}}{460 \text{ W}} \times 100 = 2.17\%$   
output power =  $10 \times 10^{-3} \text{ W}$

Q3)  $\Delta k = 0$  for direct bandgap  $\rightarrow \text{GaAs, AlGaAs, GaN}$   
 $\Delta k \neq 0$  for indirect " material  $\rightarrow \text{Si, Ge}$

For Light emitting diode material  $\rightarrow$  Direct band gap material.

as  $\Delta k = 0$  (no loss of energy during recombination of e' and holes).



Q4)  $R = \left| \frac{n_1 - n_2}{n_1 + n_2} \right|^2 = \left| \frac{3.6 - 1}{3.6 + 1} \right|^2 = \left| \frac{2.6}{4.6} \right|^2 = 0.319$  or 31.9 %

Q5)  $J_{th} = \frac{\Delta n e}{\tau} = \frac{2.02 \times 10^{18} \text{ cm}^{-3} \times 1.6 \times 10^{-19} \text{ C}}{4 \times 10^{-9}} = 8.08 \times 10^8 \frac{\text{A}}{\text{cm}^2}$ ,  $J_{th} = \frac{\Delta n e d}{\tau}$

(a) If  $d = 0.1 \mu\text{m} = 10^{-5} \text{ cm} \Rightarrow J_{th} = 8.08 \times 10^8 \times 10^{-5} \text{ A/cm}^2 = 8.08 \times 10^3 \text{ A/cm}^2$

(b) If  $d = 0.1 \mu\text{m} = 10^{-5} \text{ cm} \Rightarrow J_{th} = 8.08 \times 10^3 \text{ A/cm}^2$

(c) If  $d = 10 \text{ nm} = 10^{-6} \text{ cm} \Rightarrow J_{th} = 8.08 \times 10^2 \text{ A/cm}^2$

Q6)  $E_g = \frac{hc}{\lambda} = \frac{6.626 \times 10^{-34} \times 3 \times 10^8}{1.55 \times 10^{-6} \times 1.6 \times 10^{-19}} \text{ eV} = 0.8 \text{ eV}$

Note  $\rightarrow E_g(\text{eV}) = \frac{1.242}{\lambda(\mu\text{m})}$

Q7) (i)  $x = 0.1 \Rightarrow E_g = 1.424 + 1.266 \times 0.1 = 1.55 \text{ eV} \Rightarrow \lambda = 8013 \text{ \AA}$

(ii)  $x = 0.2 \Rightarrow E_g = 1.424 + 1.266 \times 0.2 = 1.677 \text{ eV} \Rightarrow \lambda = 7406 \text{ \AA}$

For AlAs  $\Rightarrow x = 1 \Rightarrow E_g = 2.69 \text{ eV} \Rightarrow \lambda = 4617 \text{ \AA}$

For GaAs  $\Rightarrow x = 0 \Rightarrow E_g = 1.424 \text{ eV} \Rightarrow \lambda = 8722 \text{ \AA}$

Q8)  $(E_g)_{eff} = (E_g)_{bulk} + \frac{\hbar^2}{8m_c L^2} + \frac{\hbar^2}{8m_v L^2} \Rightarrow (E_g)_{bulk} + \left( \frac{1}{m_c} + \frac{1}{m_v} \right) \frac{\hbar^2}{8 L^2}$

here  $\left( \frac{1}{m_c} + \frac{1}{m_v} \right) \frac{\hbar^2}{8} = 6.445 \times 10^{-18} \text{ eV-m}^2$ ,  $(E_g)_{bulk} = 1.424 \text{ eV}$

Case-II  $L = 10 \text{ nm} \Rightarrow (E_g)_{eff} = 1.424 \text{ eV} + \frac{6.445 \times 10^{-18}}{10^{-16}} \text{ eV} = 1.424 + 0.06445 = 1.48845 \text{ eV}$

and  $\lambda = 8344 \text{ \AA}$

Case-I  $L = 1 \mu\text{m} \Rightarrow (E_g)_{eff} \approx 1.424 \text{ eV} \Rightarrow \lambda = 8722 \text{ \AA}$

Case-III  $L = 1 \text{ nm} \Rightarrow (E_g)_{eff} = 7.869 \text{ eV} \Rightarrow \lambda = 1578 \text{ \AA} \Rightarrow$  Quantum dot effect.